Abstracts

Modeling of current lag in GaAs IC's

W.R. Curtice, J.R. Bennett, D. Suda and B.A. Syrett. "Modeling of current lag in GaAs IC's." 1998 MTT-S International Microwave Symposium Digest 98.2 (1998 Vol. II [MWSYM]): 603-606.

Leakage currents, thermal effects and deep-level traps cause significant current lag effects in GaAs MESFETs. A conventional, MESFET large-signal, equivalent-circuit model has been modified to simulate these effects and used to improve the design of GaAs digital control and RF switching circuits. Both gate lag and drain lag are simulated as well as over-shoot or under-shoot behavior.

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